

TL0375J 2.0 – 5.0 GHz GaAs Ultra Low Noise Amplifier

Application Note: TL0375J EVB E

Application Note 4700MHz~6000MHz 5.0V 70mA

Rev-1.0

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Tagore Technology

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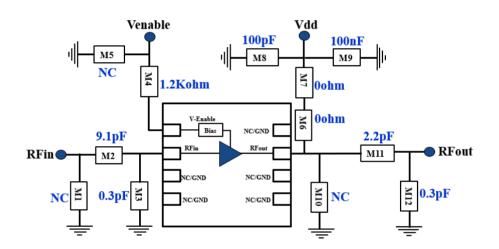


1. General Description

The TL0375J is a broadband, ultra-low Noise Amplifier (LNA) providing high gain and linearity. With a simple input and output match, this LNA can be tuned for different frequency bands targeting LTE (small cells and infrastructure) and any other applications requiring low noise, high gain, and linearity. For > 3GHz frequency band, TL0375J can be considered. The TL0375J is packaged in a compact, low-cost Dual Flat No Lead (DFN) 2x2x0.75mm, 8 pin plastic package.

TL0375J-EVB-E is an evaluation board specially tuned for frequency range of 4700MHz~6000MHz applications. Its high gain, low noise performance makes it suitable for application of public safety, radar, tactical radio, IoT, Cellular infrastructure, LTE etc.

2. TL0375J-EVB-E Board Details



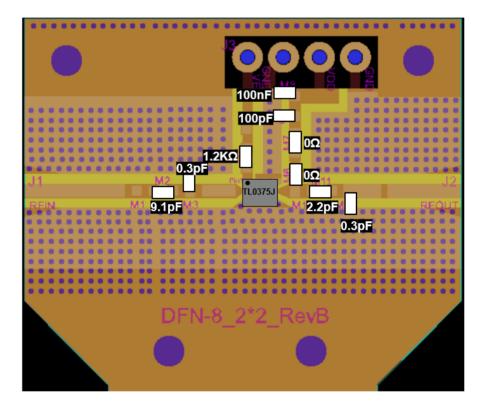


Figure 2.1 TL0375J-EVB-E 4700MHz ~ 6000MHz Schematic and EVB Layout



3. TL0375J-EVB-E Bill of Material

Component ID	Value	Manufacturer Recommended Part Num		
M2	9.1pF	Murata GJM1555C1H9R1BE		
M4	1.2ΚΩ	Panasonic	ERJ-2RKF1201X	
M3	0.3pF	Murata	GJM1555C1HR30BB01	
M8	100pF	AVX	04025A101JAT4A	
M9	100nF	TDK	C1005X7R1H104K050BE	
M6, M7	0Ω	Panasonic	ERJ-2GE0R00X	
M11	2.2pF	Murata	GJM1555C1H2R2BB01	
M12	0.3pF	Murata	GJM1555C1HR30BB01	
Q1	GaAs LNA	Tagore Technology	TL0375J	
PCB		Rogers RO4350B, 20 mils, 1 oz copper		

Table 3.1 TL0375J-EVB-E BOM

4. TL0375J-EVB-E Biasing Sequence

Turn ON Device	Turn OFF Device
1. Set Venable to +5V	1. Turn RF power off
2. Set V _{DD} to +5V	2. Turn off V _{DD}
3. Device will draw required I _{DQ} current	3. Turn off Venable
4. Apply RF power	

Table 4.1 TL0375J-EVB-E Bias and Sequencing

5. <u>TL0375J-EVB-E Board Measurement Summary</u>

Frequency (MHz)	De-embedded Noise Figure (dB)	Gain (dB)	OP1 (dBm)	OIP3(dBm) Fspacing:1MHz 0dBm Pout/tone	S11 (dB)	S22 (dB)	Mu1
4700	0.7	14.9		31.5	-12.4	-4.5	
5000	0.7	14.8		32.0	-12.4	-5.4	
5200	0.8	14.8		32.0	-13.3	-5.7	
5400	0.8	14.8	19-20	32.0	-15.1	-5.8	1.1
5600	0.9	14.6		33.0	-17.6	-5.9	
5800	0.8	14.4		31.6	-20.7	-6.0	
6000	1.0	14.2		31.6	-20.5	-6.0	

** Note: Trace loss is around 0.15-0.35dB. So EVB NF will lie between 0.8dB to 1.2dB.

Table 5.1 TL0375J-EVB-E Electrical Characteristics Summary



6. TL0375J-EVB-E Test Results

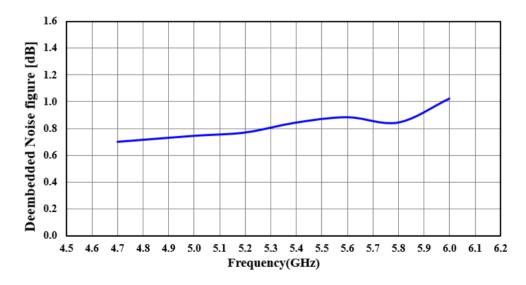
All the tests are carried out at room temperature.

6.1. S parameters



Figure 6.1.1. S parameters of TL0375J-EVB-E

6.2. De-embedded Noise Figure

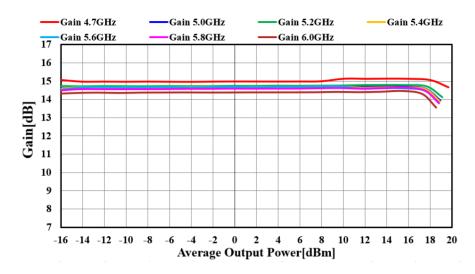


** Note: Trace loss is around 0.15-0.35dB. So EVB NF will lie between 0.8dB to 1.2dB.

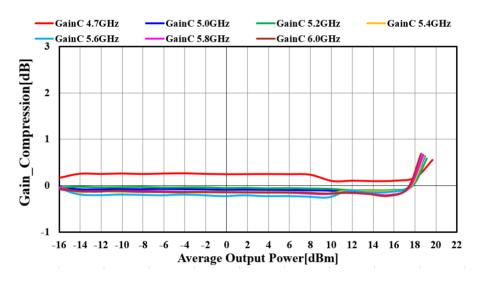
Figure 6.2.1. De-embedded Noise Figure mode of TL0375J-EVB-E



6.3. Large Signal Test Results









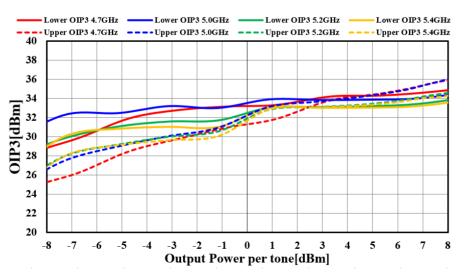


Figure 6.3.3. Output 3rd Order Intercept Point of TL0375J-EVB-E

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